

**REMARKS**

By this Amendment, claims 1 and 13 are amended, and new claims 19 and 20 are presented. Claims 1, 3-5, 7-9, 11-13 and 15-20 are pending. Reconsideration and allowance of the present application based on the following remarks are respectfully requested.

Applicant would like to thank Examiner Mondt for the courtesies extended to Applicant's representative during the June 5, 2003 personal interview. During the interview, Applicant's representative proposed amending claims 1 and 13 to recite that the plurality of first semiconductor regions and the plurality of second semiconductor regions are formed and defined respectively. Furthermore, Applicant's representative discussed further differences between the Mo et al. device and the device of the present application.

Claims 1, 3-5, 7-9, 11-13, and 15-18 were rejected under 35 U.S.C. § 102(e) over Mo et al. (U.S. Patent No. 6,429,481). Applicant respectfully traverses this rejection.

As amended, independent claims 1 and 13 recite, in part, that the plurality of first semiconductor regions and the plurality of second semiconductor regions are formed and defined respectively. As discussed during the June 5, 2003 personal interview, Mo et al. does not disclose that the n+ source contacts 16 and the n+ doped source regions 32A are formed and defined respectively. To the contrary, Mo et al. discloses that, after formation of the p+ heavy body region 34, a blocking mask is used in n-type doping to form the n+ source contacts 16 and the n+ doped source regions 32A (see column 7, lines 43-52 and Fig. 4I). Accordingly, Mo et al. does not disclose that the plurality of first semiconductor regions and the plurality of second semiconductor regions are formed and defined respectively, as recited in independent claims 1 and 13.

Dependent claims 3-5, 7-9, 11, 12 and 15-18 are believed allowable by virtue of their dependence from claims 1 and 13 for at least the reasons presented above, in addition to their recitation of independent patentable subject matter. Accordingly, Applicant respectfully submits that the rejection is overcome.

By this Amendment, new claims 19 and 20 are presented. As agreed during the interview, the P+ regions 34 in Mo et al. are contiguous in the direction of the rows 20 in Mo et al., in contrast to the P regions 32 in the specification, which are not contiguous in said direction. Accordingly, Applicants submit that Mo et al. does not disclose a plurality of noncontiguous third semiconductor regions of the first conductivity type whose major extension is in a direction parallel to both the major surface of the body region and the trench

gates, as recited in new dependent claims 19 and 20. Therefore, Applicants submit that new claims 19 and 20 are patentable over the prior art of record.

In view of the foregoing, all the claims are now believed to be in form for allowance, and such action is hereby solicited. If any point remains in issue which the Examiner feels may be best resolved through a personal or telephone interview, please contact the undersigned at the telephone number listed below.

All objections and rejections having been addressed, it is respectfully submitted that the present application is in a condition for allowance and a Notice to that effect is earnestly solicited.

Respectfully submitted,

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